

EAST - [3239.wsp:1]

File View Edit Tools Window Help

Active

- ✓ L6: (6331) ((fer\$10 "FeRAM") near3 capacitor)
- ✓ L7: (6331) ((fer\$10 "FeRAM") near3 capacitor) 6 and (electrode plate)
- ✓ L8: (3545) 7 and dielectric
- ✓ L9: (1534) 8 and barrier
- ✓ L10: (1155) 9 and oxygen
- ✓ L11: (201) 10 and (seed liner lining)
- ✓ L12: (197) 11 and ((top bottom first second lower upper) near4 (electrode plate))
- ✓ L13: (133) 12 and ((top bottom first second lower upper) near4 (barrier))
- ✓ L14: (65) 13 and (glue adhes\$4)

Failed

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QBs: US:PGPH:USPAT:ERO:JPO

Default operator: OR

13 and (glue adhes\$4)

BRIS form ISIRI form Image Text HTML

	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	6
1	r	US 2004023	2004112	14	MEMORY ARCHITECT	257/295			Wohlfahrt, Joerg et	✓	✓	✓	✓	✓	✓
2	r	US 2004020	2004102	22	Low temperature chemica	438/3	438/240;		Hintermaier, Frank	✓	✓	✓	✓	✓	✓
3	r	US 2004016	2004082	66	Manufacturing method of	438/3	257/E21.0		Sashida, Naoya et al	✓	✓	✓	✓	✓	✓
4	r	US 2004015	2004080	10	FERROELECTRIC ME	257/306	257/310;		Lee, Kyu-Mann	✓	✓	✓	✓	✓	✓
5	r	US 2004007	2004041	13	Ferroelectric capacitor m	438/396			Lung, Hsiang-Lan	✓	✓	✓	✓	✓	✓
6	r	US 2004007	2004041	14	Ferroelectric device and	257/295	257/E21.0		Lung, Hsiang-Lan	✓	✓	✓	✓	✓	✓
7	r	US 2004005	2004032	13	SERIES MEMORY ARC	257/295			Wohlfahrt, Joerg	✓	✓	✓	✓	✓	✓
8	r	US 2004005	2004032	13	MEMORY ARCHITECT	257/295	257/E21.6		Jacob, Michael et al	✓	✓	✓	✓	✓	✓
9	r	US 2004004	2004031	47	Semiconductor device an	257/200			Sashida, Naoya	✓	✓	✓	✓	✓	✓
10	r	US 2003023	2003122	15	Memory integrated circui	713/322			Jacob, Michael	✓	✓	✓	✓	✓	✓
11	r	US 2003022	2003120	17	Ferroelectric memory inte	257/200	257/E21.6		Jacob, Michael et al	✓	✓	✓	✓	✓	✓
12	r	US 2003021	2003112	20	Ferroelectric capacitor, m	257/295	257/306;		Hase, Takashi	✓	✓	✓	✓	✓	✓

	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	3
24	r	US 6872995	2005032	19	Ferroelectric capacitor, m	257/295	257/310;		Hase; Takashi	✓	✓	✓	✓	✓	✓
25	r	US 6858890	2005022	16	Ferroelectric memory inte	257/296	257/303;		Jacob; Michael et al	✓	✓	✓	✓	✓	✓
26	r	US 6800890	2004100	13	Memory architecture wit	257/295	257/200;		Wohlfahrt; Joerg et	✓	✓	✓	✓	✓	✓
27	r	US 6798010	2004092	9	Ferroelectric memory dev	257/310	257/532;		Lee; Kyu-Mann	✓	✓	✓	✓	✓	✓
28	r	US 6795329	2004092	15	Memory integrated circui	365/145	365/149		Jacob; Michael	✓	✓	✓	✓	✓	✓
29	r	US 6764862	2004072	16	Method of forming ferroe	438/3	438/238;		Park; Kun-Sang et a	✓	✓	✓	✓	✓	✓
30	r	US 6730523	2004050	23	Low temperature chemica	438/3	257/E21.2		Hintermaier; Frank	✓	✓	✓	✓	✓	✓
31	r	US 6724026	2004042	13	Memory architecture wit	257/295	257/296;		Jacob; Michael et al	✓	✓	✓	✓	✓	✓
32	r	US 6720598	2004041	13	Series memory architectu	257/295	257/296;		Wohlfahrt; Joerg	✓	✓	✓	✓	✓	✓
33	r	US 6708405	2004032	15	Method for producing an	29/852	216/18;		Hasler; Barbara et a	✓	✓	✓	✓	✓	✓
34	r	US 6699725	2004030	10	Methods of fabricating fe	438/3	257/E21.0		Lee; Kyu-Mann	✓	✓	✓	✓	✓	✓
35	r	US 6635528	2003102	22	Method of planarizing a c	438/253	257/E21.3		Gilbert; Stephen R.	✓	✓	✓	✓	✓	✓
36	r	US 6611449	2003082	11	Contact for memory cells	365/145	257/E21.6		Hilliger; Andreas	✓	✓	✓	✓	✓	✓
37	r	US 6600183	2003072	20	Integrated circuit capacit	257/295	257/310;		Visokay; Mark R. et	✓	✓	✓	✓	✓	✓
38	r	US 6576546	2003061	21	Method of enhancing adh	438/629	257/E21.2		Gilbert; Stephen R.	✓	✓	✓	✓	✓	✓
39	r	US 6555431	2003042	20	Method for forming integ	438/253	257/E21.0		Xing; Guoqiang et a	✓	✓	✓	✓	✓	✓
40	r	US 6538272	2003032	15	Semiconductor storage de	257/295	257/303;		Yamazaki; Shinobu	✓	✓	✓	✓	✓	✓
41	r	US 6534809	2003031	22	Hardmask designs for dry	257/295	257/751;		Moise; Theodore et	✓	✓	✓	✓	✓	✓
42	r	US 6444542	2002090	42	Integrated circuit and met	438/448	257/E21.0		Moise; Theodore S.	✓	✓	✓	✓	✓	✓
43	r	US 6350643	2002022	16	Reduced degradation of	438/240	257/E21.2		Hintermaier; Frank	✓	✓	✓	✓	✓	✓
44	r	US 6344413	2002020	15	Method for forming a se	438/678	438/240;		Zurcher; Peter et al	✓	✓	✓	✓	✓	✓

	U	1	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	4
46	r	r	US 6294425	2001092	25	Methods of forming integ	438/253	257/306;		Hideki; Horii	r	r	r	r	r	r
47	r	c	US 6271136	2001080	8	Multi-step plasma proces	438/687	257/E21.1		Shue; Shau-Lin et a	r	r	r	r	r	r
48	r	r	US 6242321	2001060	12	Structure and fabrication	438/424	257/E21.0		Acosta; Raul Edmu	r	r	r	r	r	r
49	r	r	US 6211035	2001040	42	Integrated circuit and met	438/396	257/E21.0		Moise; Theodore S.	r	r	r	r	r	r
50	r	r	US 6177351	2001012	28	Method and structure for	438/694	257/E21.0		Beratan; Howard R.	r	r	r	r	r	r
51	r	r	US 6153490	2000112	20	Method for forming integ	438/396	257/E21.0		Xing; Guoqiang et a	r	r	r	r	r	r
52	r	r	US 6090697	2000071	20	Etchstop for integrated ci	438/618	257/E21.0		Xing; Guoqiang et a	r	r	r	r	r	r
53	r	r	US 6010744	2000010	9	Method for nucleation co	427/81	257/E21.2		Buskirk; Peter Van	r	r	r	r	r	r
54	r	r	US 5851896	1998122	15	Conductive exotic-nitride	438/396	257/E21.0		Summerfelt; Scott	r	r	r	r	r	r
55	r	c	US 5811851	1998092	10	Pre-oxidizing high-dielect	257/310	257/295;		Nishioka; Yasushiro	r	r	r	r	r	r
56	r	r	US 5757612	1998052	10	Structure and fabrication	361/321.4	257/303;		Acosta; Raul Edmu	r	r	r	r	r	r
57	r	r	US 5729054	1998031	16	Conductive noble-metal-i	257/751	257/295;		Summerfelt; Scott	r	r	r	r	r	r
58	r	r	US 5696018	1997120	16	Method of forming condu	438/396	257/E29.3		Summerfelt; Scott	r	r	r	r	r	r
59	r	c	US 5679980	1997102	14	Conductive exotic-nitride	257/751	257/295;		Summerfelt; Scott	r	r	r	r	r	r
60	r	r	US 5665628	1997090	16	Method of forming condu	438/3	257/E21.0		Summerfelt; Scott	r	r	r	r	r	r
61	r	r	US 5585300	1996121	16	Method of making condu	505/330	257/E21.0		Summerfelt; Scott	r	r	r	r	r	r
62	r	r	US 5554866	1996091	11	Pre-oxidizing high-dielect	257/295	257/310;		Nishioka; Yasushiro	r	r	r	r	r	r
63	r	c	US 5554564	1996091	11	Pre-oxidizing high-dielect	438/396	257/E21.0		Nishioka; Yasushiro	r	r	r	r	r	r
64	r	r	US 5504041	1996040	15	Conductive exotic-nitride	438/396	257/E21.0		Summerfelt; Scott	r	r	r	r	r	r
65	r	r	US 5489548	1996020	11	Method of forming high-	438/396	257/E21.0		Nishioka; Yasushiro	r	r	r	r	r	r